

N-channel TrenchMOS SiliconMAX standard level FET Rev. 4 — 27 December 2011 Product de

Product data sheet

Product profile 1.

1.1 General description

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

High frequency computer motherboard OR-ing applicationss **DC-to-DC convertors**

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	75	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	230	W
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	-	7.5	8.8	mΩ
Dynamic	characteristics					
Q_{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 75 A; V _{DS} = 80 V; T _j = 25 °C; see <u>Figure 11</u>	-	44	-	nC

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2. Pinning information

Table 2.	Pinning information						
Pin	Symbol	Description	Simplified outline	Graphic symbol			
1	G	gate		-			
2	D	drain	mb				
3	S	source					
mb	D	mounting base; connected to drain		mbb076 S			

SOT78 (TO-220AB)

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN009-100P	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	T _j ≤ 175 °C; T _j ≥ 25 °C; R _{GS} = 20 kΩ	-	100	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	-	65	А
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 3}};$	-	75	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	400	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	230	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
V _{GSM}	peak gate-source voltage	pulsed; $t_p \le 50 \ \mu s$; $T_j \le 150 \ ^\circ C$; $\delta = 25 \ \%$	-30	30	V
Source-dra	in diode				
I _S	source current	T _{mb} = 25 °C	-	75	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	400	А
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ V_{GS} = 10 \text{ V}; \text{T}_{j(init)} = 25 \text{ °C}; \text{I}_\text{D} = 35 \text{ A}; \\ V_{sup} = 15 \text{ V}; \text{ unclamped}; \text{t}_\text{p} = 0.1 \text{ ms}; \\ R_{GS} = 50 \Omega $	-	120	mJ
I _{DS(AL)S}	non-repetitive drain-source avalanche current	V_{GS} = 10 V; V_{sup} = 15 V; R_{GS} = 50 Ω ; $T_{j(init)}$ = 25 °C; unclamped	-	75	A
-					

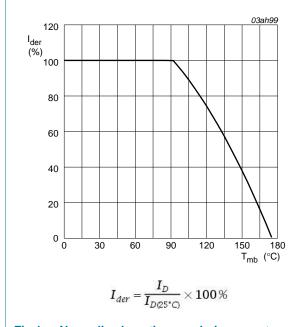
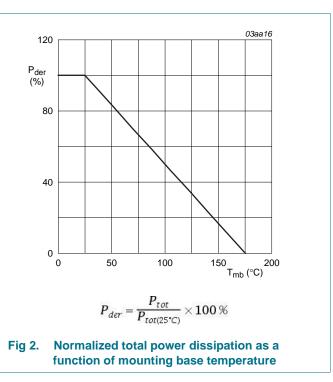


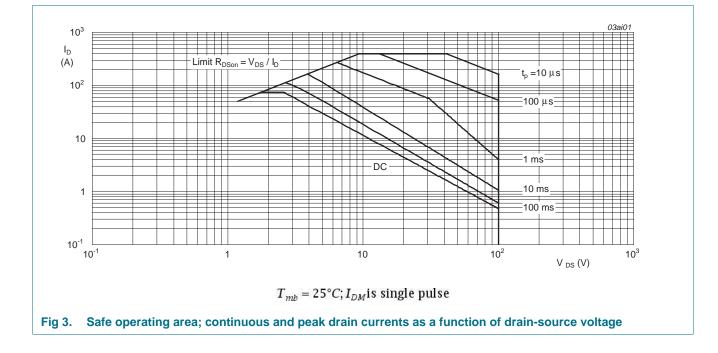
Fig 1. Normalized continuous drain current as a function of mounting base temperature



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PSMN009-100P

PSMN009-100P



5. Thermal characteristics

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.65	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W

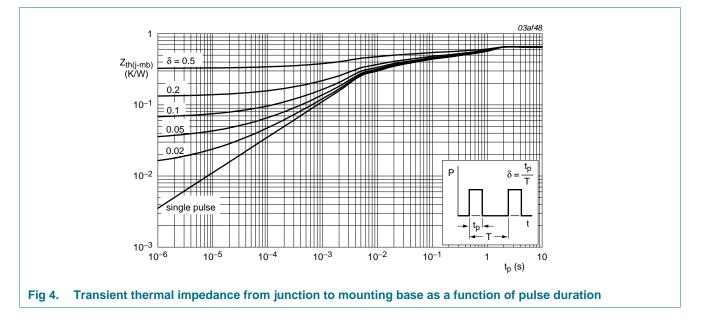
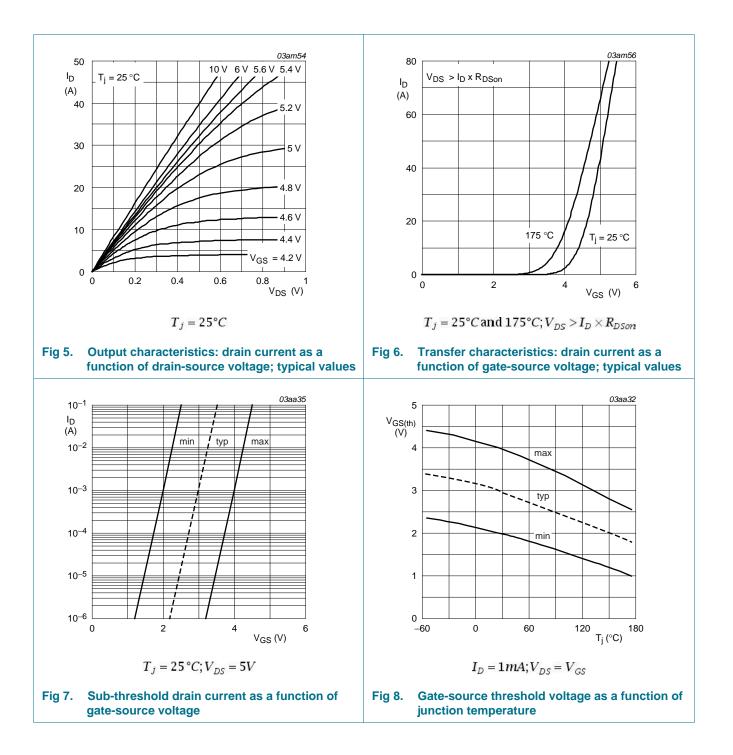


Table 5. Thermal characteristics

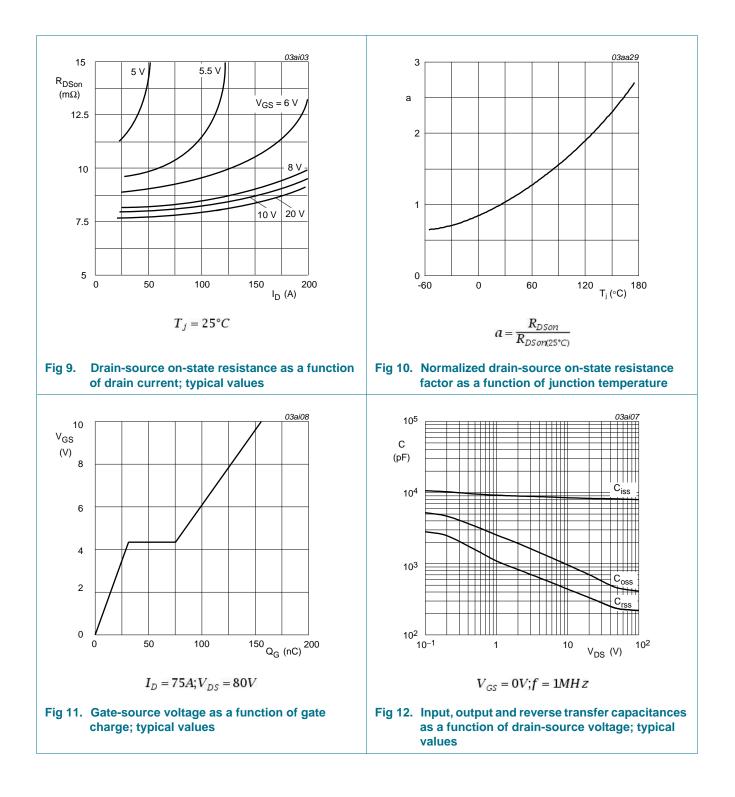
6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = 0.25 mA; V_{GS} = 0 V; T_j = -55 °C	90	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 8</u>	1	1	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see Figure 8	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 8	-	-	4.4	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	20.25	23.8	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 9; see Figure 10	-	7.5	8.8	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 75 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$	-	156	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; see <u>Figure 11</u>	-	31	-	nC
Q _{GD}	gate-drain charge		-	44	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	8250	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{\text{Figure } 12}$	-	620	-	pF
C _{rss}	reverse transfer capacitance		-	300	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; R_{L} = 1.25 Ω ; V_{GS} = 10 V;	-	38	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 \text{ °C}; I_D = 12 \text{ A}$	-	59	-	ns
t _{d(off)}	turn-off delay time		-	120	-	ns
t _f	fall time		-	43	-	ns
Source-d	rain diode					
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 13</u>	-	0.8	1.2	V

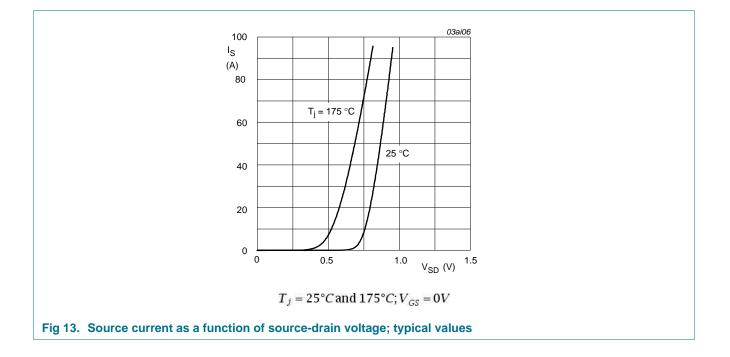
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Package outline 7.

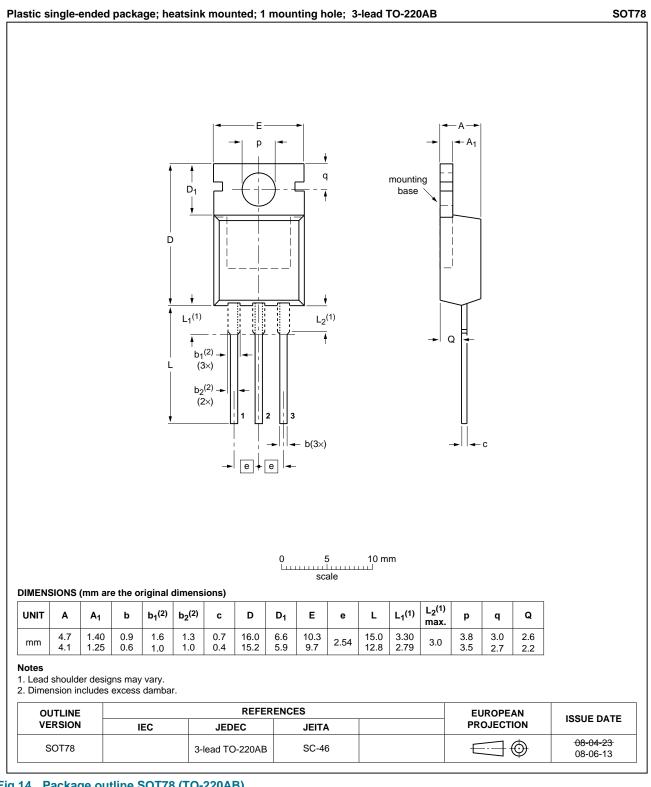


Fig 14. Package outline SOT78 (TO-220AB)

PSMN009-100P **Product data sheet**

8. Revision history

Table 7.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN009-100P v.4	20111227	Product data sheet	-	PSMN009-100P v.3
Modifications:	 Various changes 	s to content.		
PSMN009-100P v.3	20111121	Product data sheet	-	PSMN009-100P v.2

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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